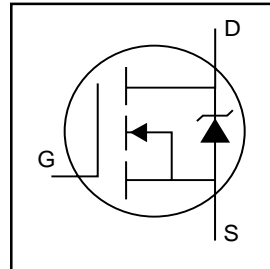


- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

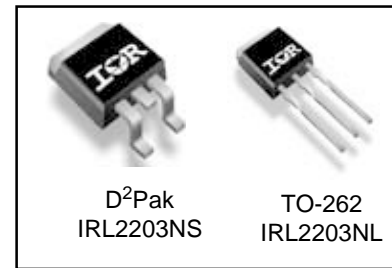


$V_{DSS} = 30V$
$R_{DS(on)} = 7.0m\Omega$
$I_D = 116A\textcircled{7}$

**Description**

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application. The through-hole version (IRL2203NL) is available for low-profile applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	116 <sup>⑦</sup>	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	82	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	400	
$P_D @ T_A = 25^\circ C$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ C$	Power Dissipation	180	W
	Linear Derating Factor	1.2	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$I_{AR}$	Avalanche Current <sup>①</sup>	60	A
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	18	mJ
dv/dt	Peak Diode Recovery dv/dt <sup>③</sup>	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

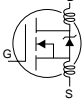
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.85	°C/W
$R_{\theta JA}$	Junction-to-Ambient(PCB Mounted,steady-state) <sup>⑥</sup>	—	40	

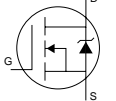
# IRL2203NS/IRL2203NL

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IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$	
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$	
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	7.0	m $\Omega$	$V_{GS} = 10V, I_D = 60A$ ④	
		—	—	10		$V_{GS} = 4.5V, I_D = 48A$ ④	
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$	
$g_{fs}$	Forward Transconductance	73	—	—	S	$V_{DS} = 25V, I_D = 60A$ ④	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$	
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$	
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$	
$Q_g$	Total Gate Charge	—	—	60	nC	$I_D = 60A$	
$Q_{gs}$	Gate-to-Source Charge	—	—	14		$V_{DS} = 24V$	
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	33		$V_{GS} = 4.5V$ , See Fig. 6 and 13	
$t_{d(on)}$	Turn-On Delay Time	—	11	—		$V_{DD} = 15V$	
$t_r$	Rise Time	—	160	—	nH	$I_D = 60A$	
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		$R_G = 1.8\Omega$	
$t_f$	Fall Time	—	66	—		$V_{GS} = 4.5V$ , See Fig. 10 ④	
$L_D$	Internal Drain Inductance	—	4.5	—		Between lead, 6mm (0.25in.) from package and center of die contact	
$L_S$	Internal Source Inductance	—	7.5	—	pF		
$C_{iss}$	Input Capacitance	—	3290	—			$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1270	—			$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	170	—			$f = 1.0\text{MHz}$ , See Fig. 5
$E_{AS}$	Single Pulse Avalanche Energy②	—	1320⑤	290⑥	mJ	$I_{AS} = 60A, L = 0.16\text{mH}$	

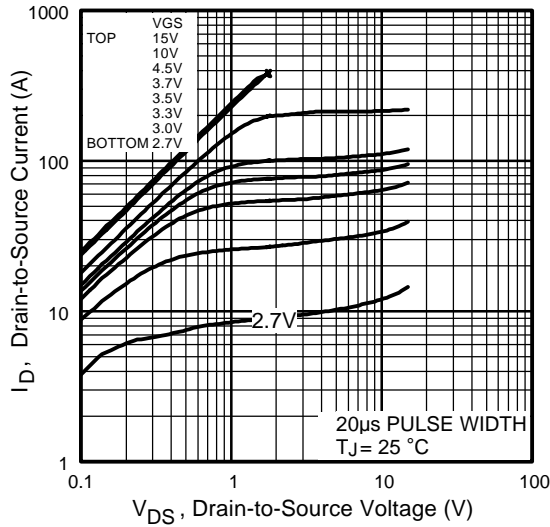
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	116⑦	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode)①	—	—	400		
$V_{SD}$	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 60A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	56	84	ns	$T_J = 25^\circ\text{C}, I_F = 60A$
$Q_{rr}$	Reverse Recovery Charge	—	110	170	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

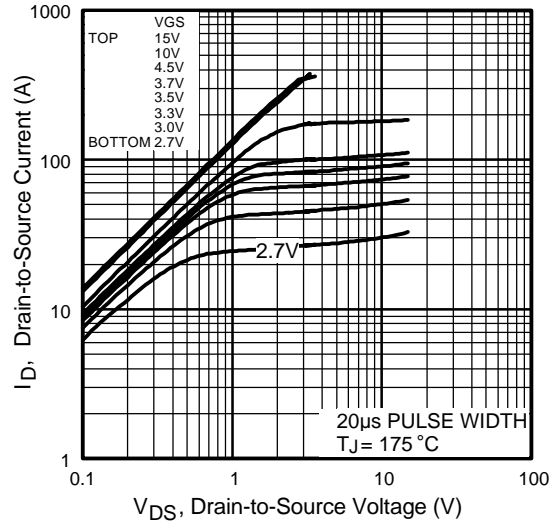
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}, L = 0.16\text{mH}, R_G = 25\Omega, I_{AS} = 60A, V_{GS} = 10V$  (See Figure 12)
- ③  $I_{SD} \leq 60A, di/dt \leq 110A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .

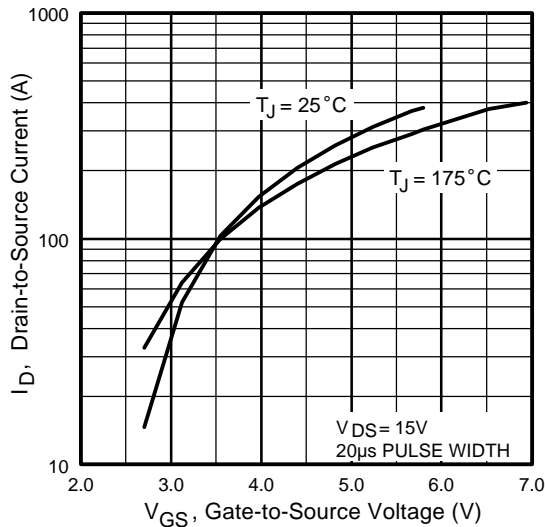
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- ⑥ This is a calculated value limited to  $T_J = 175^\circ\text{C}$ .
- ⑦ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.



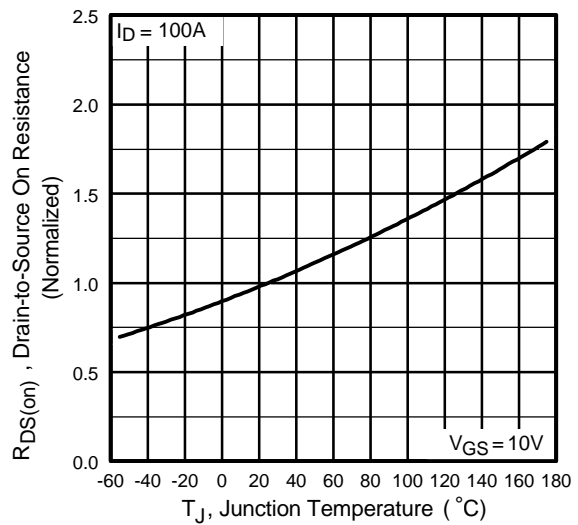
**Fig 1.** Typical Output Characteristics



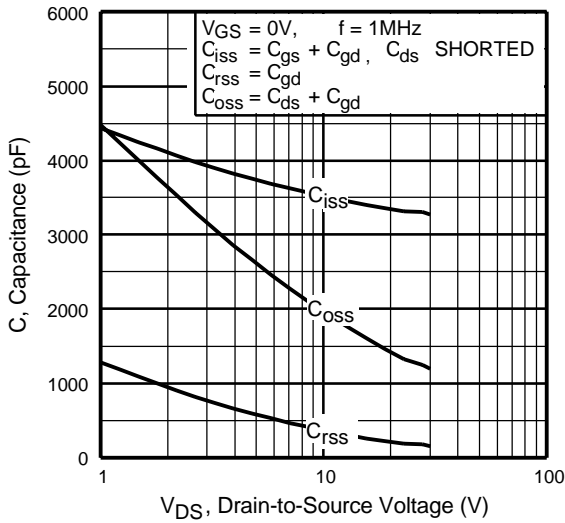
**Fig 2.** Typical Output Characteristics



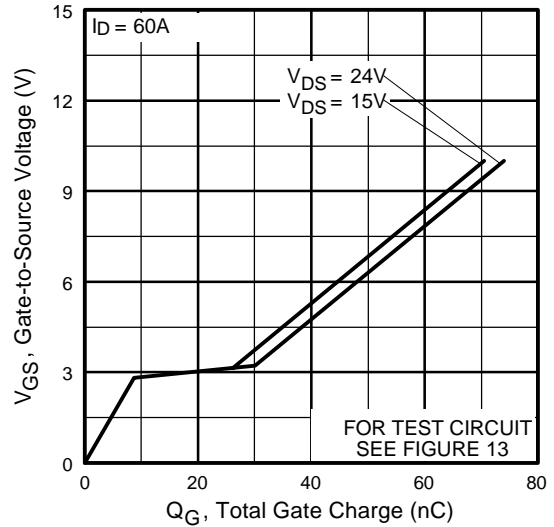
**Fig 3.** Typical Transfer Characteristics



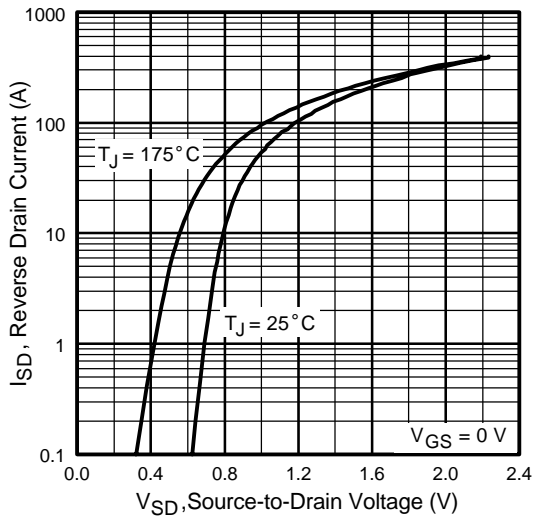
**Fig 4.** Normalized On-Resistance Vs. Temperature



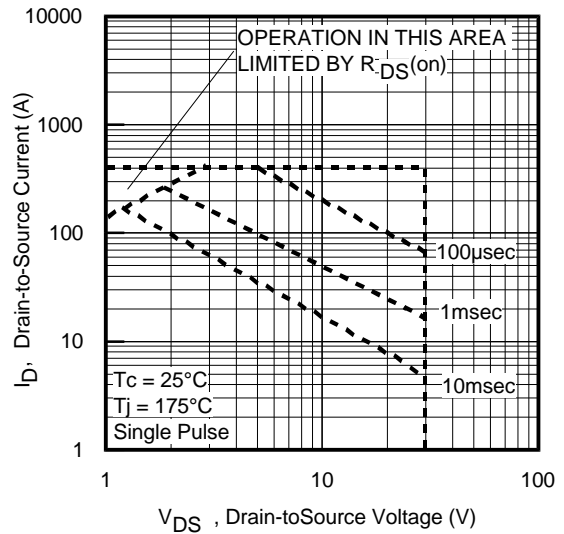
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



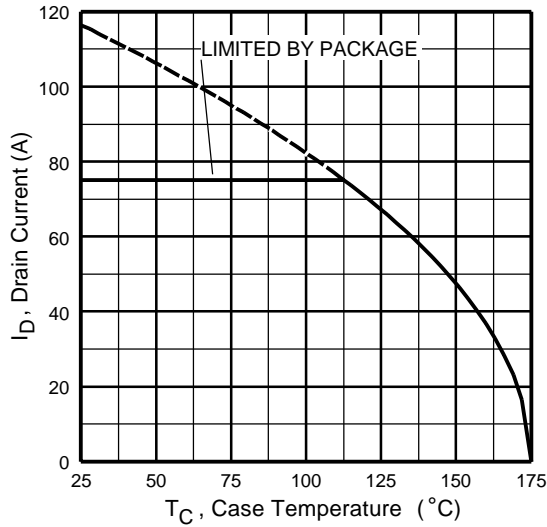
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



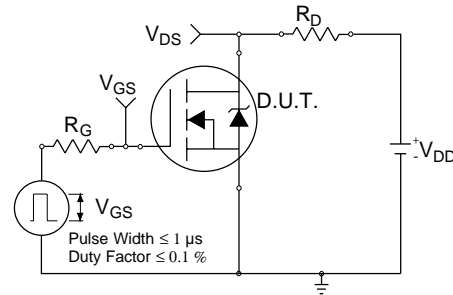
**Fig 7.** Typical Source-Drain Diode Forward Voltage



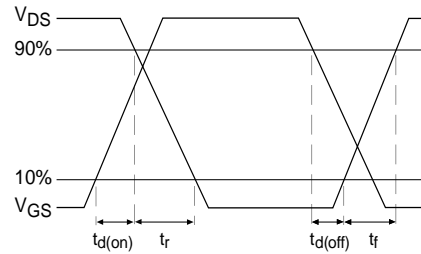
**Fig 8.** Maximum Safe Operating Area



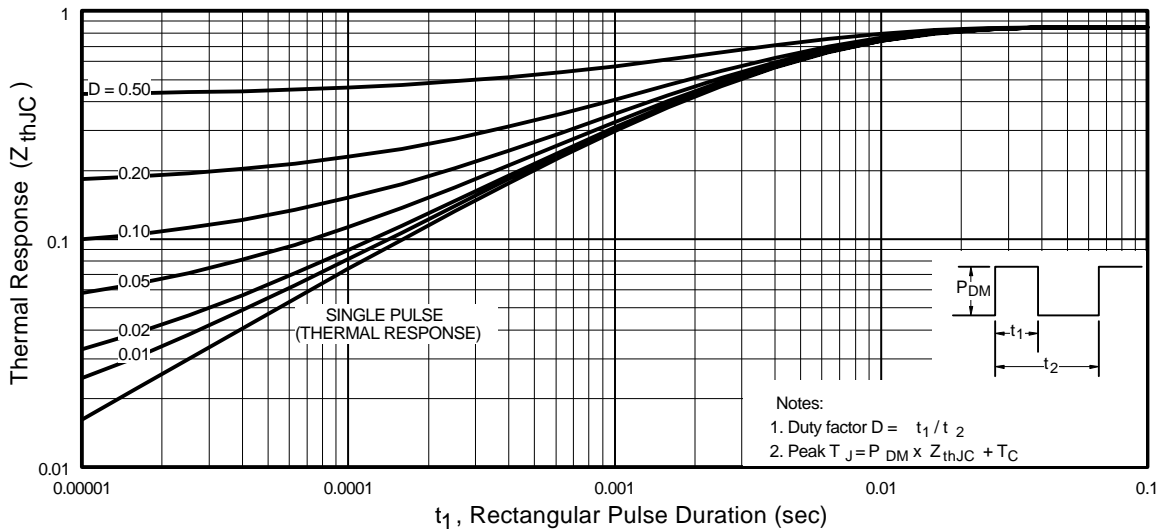
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



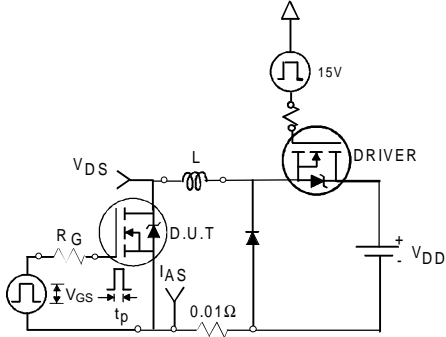
**Fig 10b.** Switching Time Waveforms



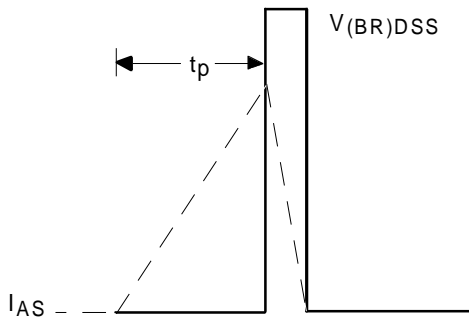
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRL2203NS/IRL2203NL

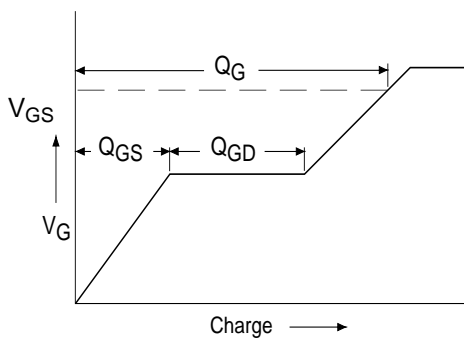
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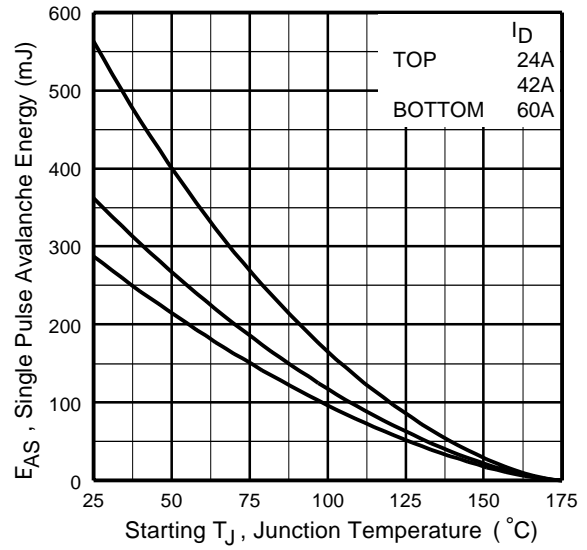
**Fig 12a.** Unclamped Inductive Test Circuit



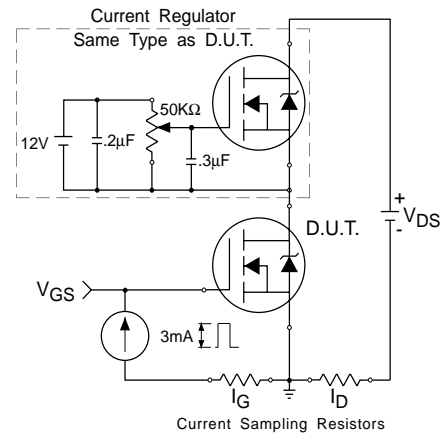
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

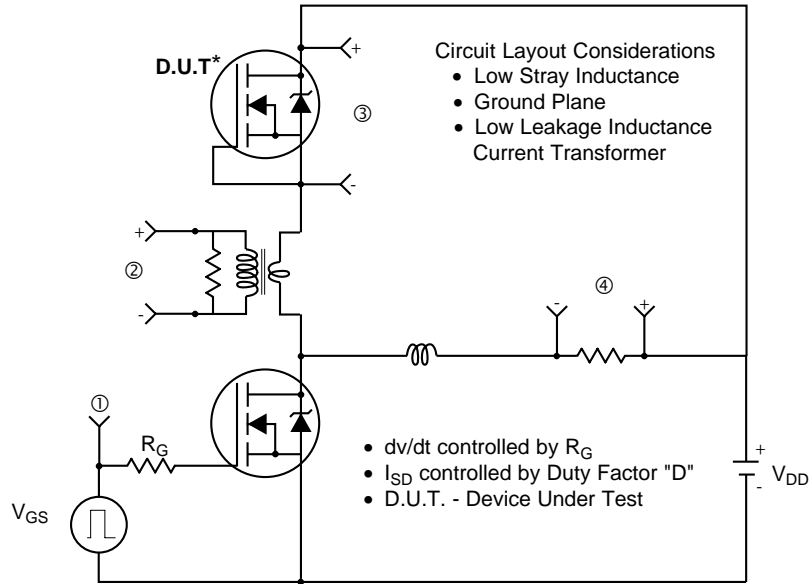


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

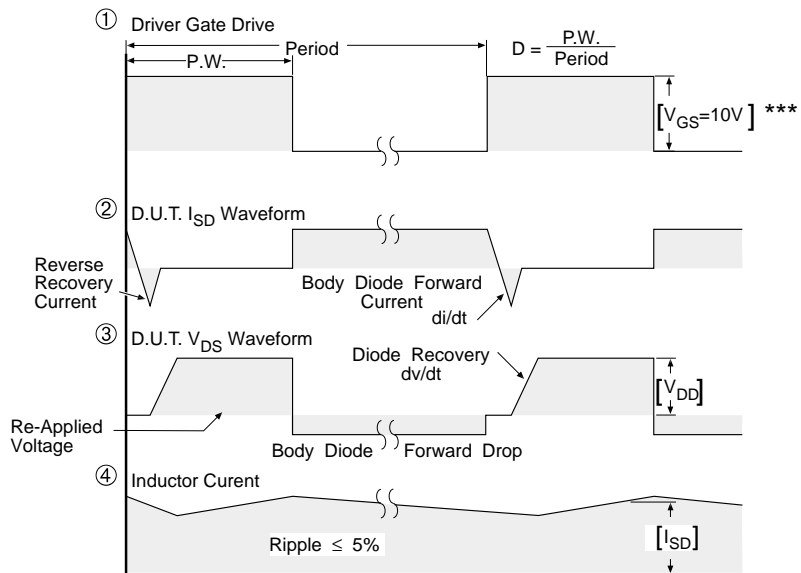


**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

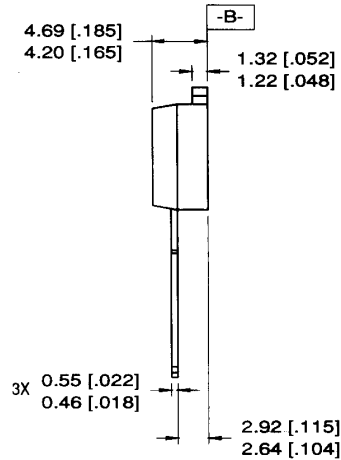
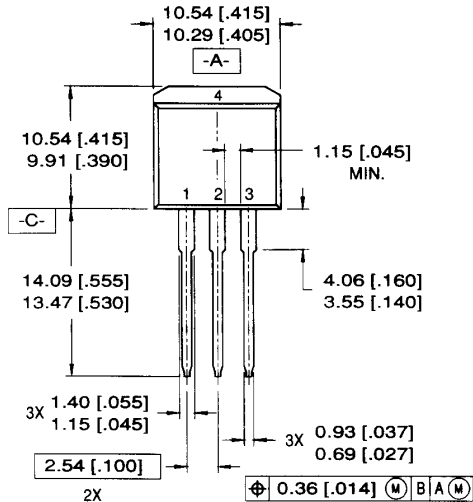
**Fig 14.** For N-channel HEXFET® power MOSFETs





## TO-262 Package Outline

Dimensions are shown in millimeters (inches)

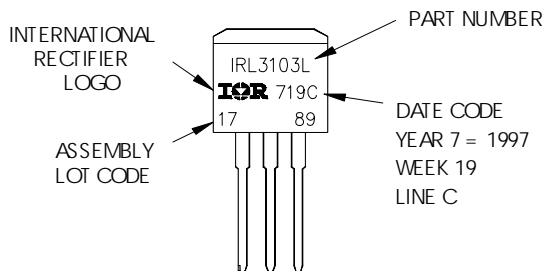


**NOTES:**

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON VW19, 1997  
 IN THE ASSEMBLY LINE "C"

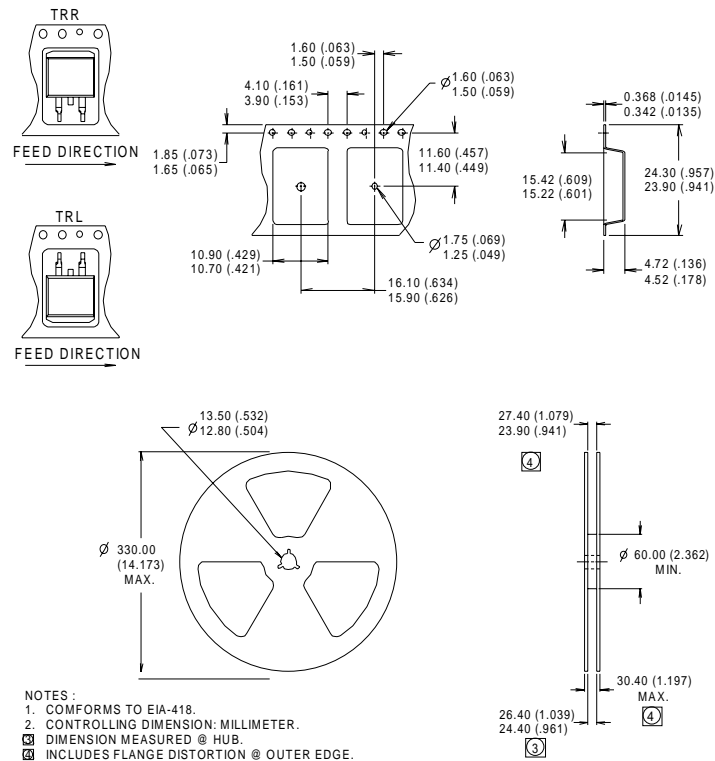


# IRL2203NS/IRL2203NL

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## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.  
This product has been designed and qualified for the Automotive [Q101] market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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